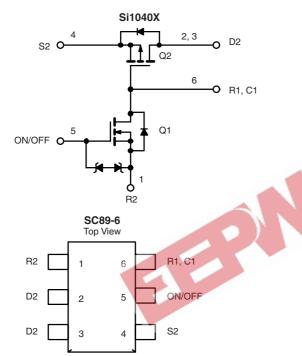




Load Switch with Level-Shift

PRODUCT SUMMARY				
V _{DS2} (V)	$R_{DS(on)}\left(\Omega\right)$ $I_{D}\left(A\right)$			
1.8 to 8	0.625 at V _{IN} = 4.5 V	± 0.43		
	0.890 at V _{IN} = 2.5 V	± 0.36		
	1.25 at V _{IN} = 1.8 V	± 0.3		



Ordering Information: Si1040X-T1-E3 (Lead (Pb)-free)

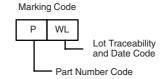
Si1040X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

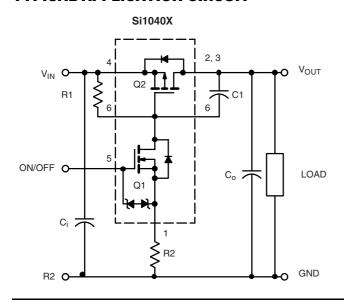
- Halogen-free Option Available
- TrenchFET® Power MOSFET
- 1.8 to 8 V Input
- 1.5 to 8 V Logic Level Control
- Smallest LITTLE FOOT® Package: 1.6 mm x 1.6 mm
- 2000 V ESD Protection On Input Switch, VON/OFF
- · Adjustable Slew-Rate

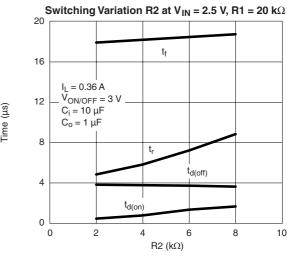
DESCRIPTION

The Si1040X includes a P- and N-Channel MOSFET in a single SC89-6 package. The low on-resistance P-Channel TrenchFET is tailored for use as a load switch. The N-Channel, with an external resistor, can be used as a level-shift to drive the P-Channel load-switch. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1040X operates on supply lines from 1.8 V to 8 V, and can drive loads up to 0.43 A.



TYPICAL APPLICATION CIRCUIT





Note: For R2 switching variations with other V_{IN}/R1 combinations See Typical Characteristics

Si1040X

Vishay Siliconix



COMPONENTS				
R1	Pull-Up Resistor	Typical 10 k Ω to 1 m Ω^a		
R2	Optional Slew-Rate Control	Typical 0 to 100 kΩ ^a		
C1	Optional Slew-Rate Control	Typical 1000 pF		

The Si1040X is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

Notes:

a. Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

Parameter		Symbol	Limit	Unit	
Input Voltage		V _{IN}	8	M	
ON/OFF Voltage		V _{ON/OFF}	8	V	
Local Ormania	Continuous ^{a, b}	- IL	± 0.43	А	
Load Current	Pulsed ^{b, c}		± 1.0		
Continuous Intrinsic Diode Conduction ^a		Is	- 0.15		
Maximum Power Dissipation ^a		P _D	0.174	W	
Operating Junction and Storage Temperature Range	A	T _J , T _{stg}	- 55 to 150	°C	
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1	500 Ω)	ESD	2	kV	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient (Continuous Current) ^a	R_{thJA}	600	720	°C/W		
Maximum Junction-to-Foot (Q2)	R_{thJC}	450	540	G/ VV		

Notes:

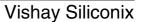
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
OFF Characteristics							
Reverse Leakage Current	I _{FL}	$V_{IN} = 8 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			1	μΑ	
Diode Forward Voltage	V_{SD}	I _S = - 0.15 A		0.85	1.2	V	
ON Characteristics							
Input Voltage Range	V_{IN}		1.8		8	V	
	R _{DS(on)}	$V_{ON/OFF} = 1.5 \text{ V}, V_{IN} = 4.5 \text{ V}, I_D = 0.43 \text{ A}$		0.500	0.625		
On-Resistance (P-Channel) at 1 A		$V_{ON/OFF} = 1.5 \text{ V}, V_{IN} = 2.5 \text{ V}, I_D = 0.36 \text{ A}$		0.710	0.890	Ω	
		$V_{ON/OFF} = 1.5 \text{ V}, V_{IN} = 1.8 \text{ V}, I_D = 0.3 \text{ A}$		1.0	1.25		
On-State (P-Channel) Drain Current		$V_{IN-OUT} \le 0.2 \text{ V}, V_{IN} = 5 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$	1			А	
On-State (F-Channel) Drain Current	I _{D(on)}	$V_{IN-OUT} \le 0.3 \text{ V}, V_{IN} = 3 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$	0.8			_ ^	

Notes:

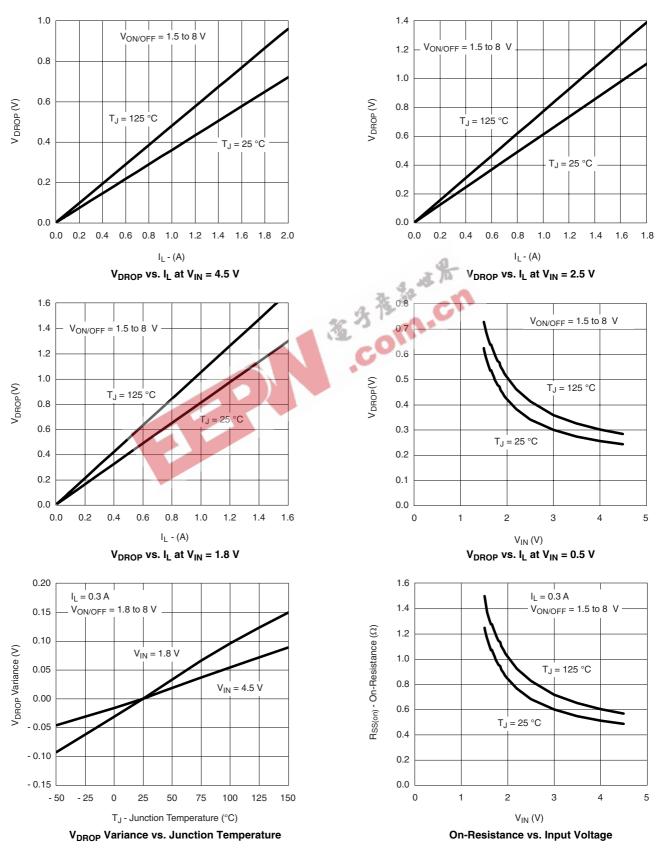
- a. Surface Mounted on FR4 board.
- b. $V_{IN} = 8 \text{ V}$, $V_{ON/OFF} = 8 \text{ V}$, $T_A = 25 \,^{\circ}\text{C}$.
- c. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

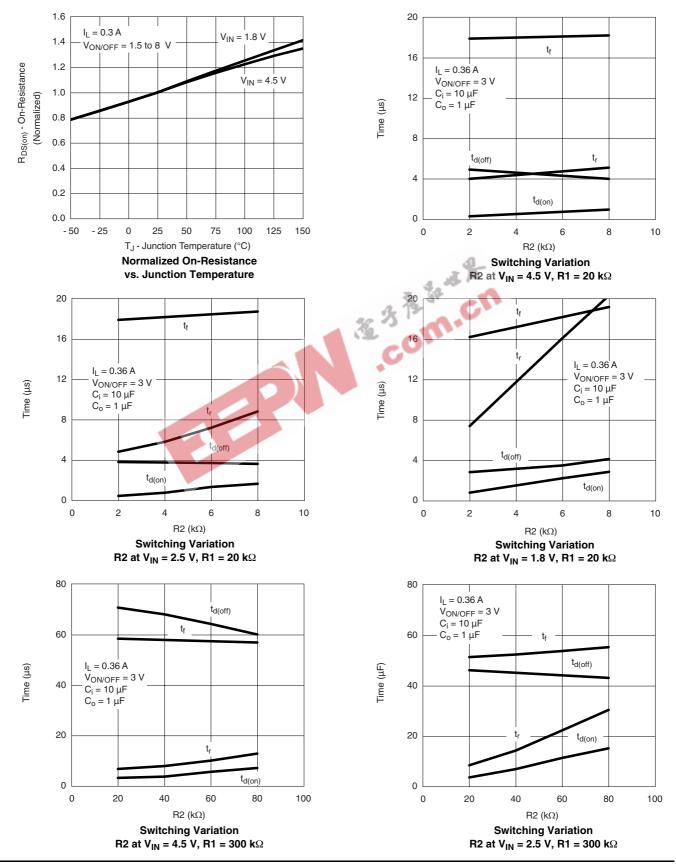


Si1040X

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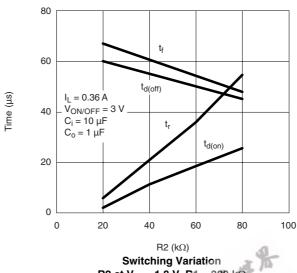


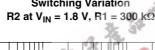
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

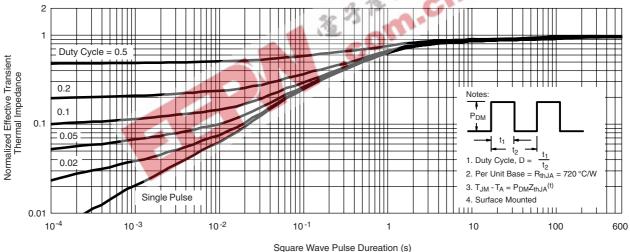




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71809.





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